

60V NPN MEDIUM POWER LOW SATURATION TRANSISTOR IN SOT223

Features

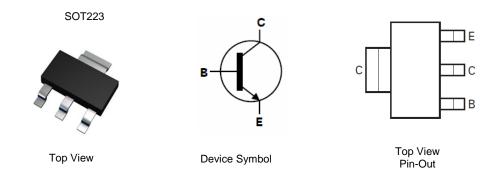
- BV_{CEO} > 60V
- I_C = 6A High Continuous Collector Current
- I_{CM} = 20A Peak Pulse Current
- Low Saturation Voltage V_{CE(sat)} < -60mV @ -1A
- $R_{SAT} = 35m\Omega$ for a Low Equivalent On-Resistance
- h_{FE} Specified up to 10A for a High Gain Hold-Up
- Complementary PNP Type: ZX5T951G
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound;
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)

Applications

- Emergency Lighting Circuits
- MOSFET & IGBT Gate Drivers
- Solenoid, Relay and Actuator Drivers
- DC Modules
- Motor Control



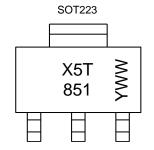
Ordering Information (Note 4)

ſ	Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
	ZX5T851GTA	AEC-Q101	X5T851	7	12	1,000
	ZX5T851GTC	AEC-Q101	X5T851	13	12	4,000

Notes:

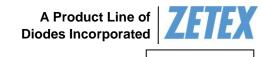
- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



X5T 851 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week Code (01~53)





Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	150	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	Ic	6	Α
Peak Pulse Current	Ісм	20	А

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		3.0		
Power Dissipation	(Note 6)	P _D	2.0	W	
Power Dissipation	(Note 7)		1.6	VV	
	(Note 8)		1.2		
	(Note 5)		41.7		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{ heta JA}$	62.5		
Thermal Resistance, Junction to Ambient	(Note 7)		78.1	°C/W	
	(Note 8)		104		
Thermal Resistance Junction to Lead (Note 9)		$R_{ hetaJL}$	10.5		
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 8)

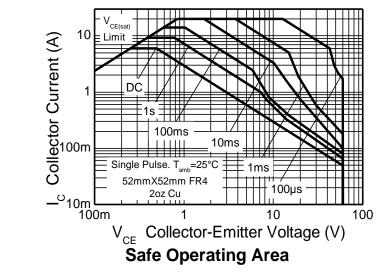
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

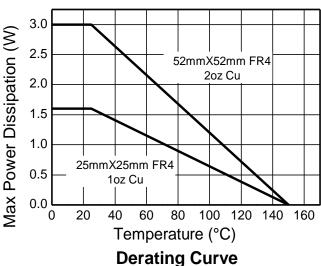
Notes:

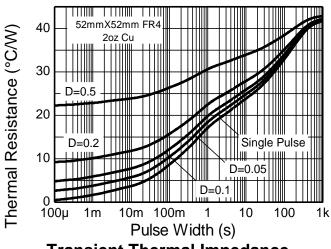
- 5. For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
- 7. Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.
- 8. Same as Note 5, except the device is mounted on minimum recommended pad layout.
- 9. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

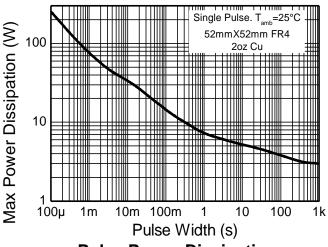


Thermal Characteristics and Derating Information









Transient Thermal Impedance

Pulse Power Dissipation





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

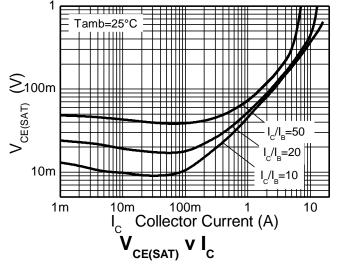
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	150	190	-	V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage	BV _{CER}	150	190	_	V	$I_C = -1\mu A, R_B \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	60	80	-	V	$I_C = 10mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.1	_	V	I _E = 100μA
Collector Cut-Off Current	Ісво	_ _	<1 -	20 0.5	nΑ μΑ	V _{CB} = 120V V _{CB} = 120V, T _A = +100°C
Collector Cut-Off Current	I _{CER} R _B ≤1kΩ	_ _	<1 -	20 0.5	nΑ μΑ	V _{CB} = 120V V _{CB} = 120V, T _A = +100°C
Emitter Cut-Off Current	I _{EBO}	_	<1	10	nA	V _{EB} = 6V
	V _{CE} (sat)	_	20	30	mV	$I_C = 100 \text{mA}, I_B = 5 \text{mA}$
		-	45	60		$I_C = 1A$, $I_B = 100mA$
Collector-Emitter Saturation Voltage (Note 11)		_	50	70		$I_C = 1A$, $I_B = 50mA$
		_	100	135		$I_C = 2A$, $I_B = 50mA$
		-	210	260		$I_C = 6A$, $I_B = 300mA$
Base-Emitter Saturation Voltage (Note 11)	$V_{BE(sat)}$	_	1000	1100	mV	$I_C = 6A, I_B = 300mA$
Base-Emitter Turn-On Voltage (Note 11)	$V_{BE(on)}$	_	940	1050	mV	$I_C = 6A$, $V_{CE} = 1V$
		100	200	-		$I_C = 10$ mA, $V_{CE} = 1$ V
DC Current Gain (Note 11)	h _{FE}	100	200	300		$I_C = 2A$, $V_{CE} = 1V$
DC Current Gain (Note 11)		55	105	-	_	$I_C = 5A$, $V_{CE} = 1V$
		20	40	_		$I_C = 10A, V_{CE} = 1V$
Output Capacitance	C_{obo}	-	31	-	pF	$V_{CB} = 10V. f = 1MHz$
Current Gain-Bandwidth Product	f _T	-	130	_	MHz	$V_{CE} = 5V, I_{C} = 100mA,$ f = 100MHz
Switching Times	t _{on}	_	42	_	ns	$I_{C} = 1A, V_{CC} = 10V,$
Owntoning rimes	t _{off}	_	760	-	110	$I_{B1} = -I_{B2} = 100 \text{mA}$

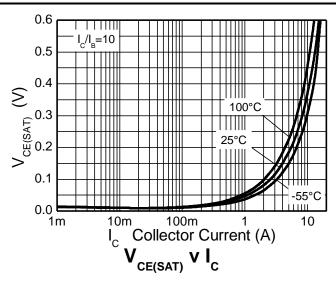
Note:

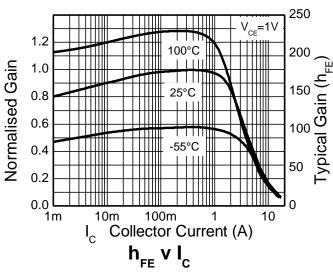
11. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

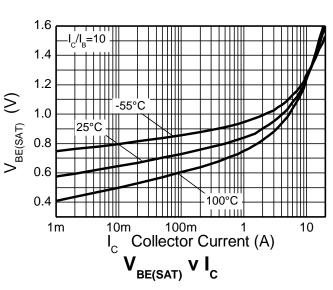


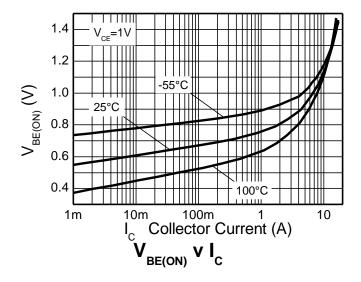
Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)









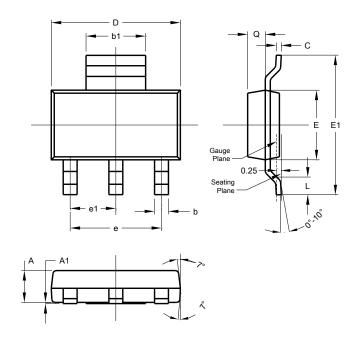






Package Outline Dimensions

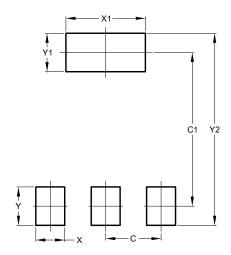
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

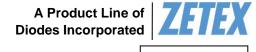
Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00





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